



### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Features**

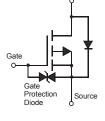
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

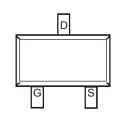
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (approximate)







Drain



Top View

**Equivalent Circuit** 

Top View

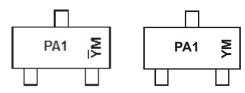
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMG1013UW-7	SOT-323	3000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

## **Marking Information**



PA1 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or  $\overline{Y}$  = Year (ex: A = 2013) M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

#### Date Code Key

Year	2008	2	009	2010	2	2011	2012		2013	2014		2015
Code	V		W	Χ		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

1 of 6 **DMG1013UW** September 2013 Document number: DS31861 Rev. 3 - 2 © Diodes Incorporated



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Char	Symbol	Value	Unit		
Drain-Source Voltage				-20	V
Gate-Source Voltage			$V_{GSS}$	±6	V
Continuous Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C	I <sub>D</sub>	-0.82 -0.54	Α
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-6	Α		

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_{D}$	0.31	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	398	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	1	1	T	1	1	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±2.0	μΑ	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	-	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
		-	0.5	0.75		$V_{GS} = -4.5V$ , $I_D = -430mA$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>		0.7	1.05	Ω	$V_{GS} = -2.5V, I_D = -300mA$
			1.0	1.5		$V_{GS} = -1.8V, I_D = -150mA$
Forward Transfer Admittance	Y <sub>fs</sub>	-	0.9	-	S	$V_{DS} = -10V, I_{D} = -250mA$
Diode Forward Voltage	$V_{SD}$		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	-	59.76	-	pF	101/11/
Output Capacitance	Coss	-	12.07	-	pF	$V_{DS} = -16V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	-	6.36	-	pF	1 = 1.0MH2
Total Gate Charge	Qg	-	622.4	-	рС	4.5)/.)/ 4.0)/
Gate-Source Charge	Qgs	-	100.3	-	рC	$V_{GS} = -4.5V, V_{DS} = -10V,$
Gate-Drain Charge	Q <sub>gd</sub>	-	132.2	-	рС	$I_D = -250 \text{mA}$
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.1	-	ns	101/11/
Turn-On Rise Time	t <sub>r</sub>	-	8.1	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t <sub>D(off)</sub>	-	28.4	-	ns	$R_L = 47\Omega, R_G = 10\Omega,$ $R_D = -200 \text{mA}$
Turn-Off Fall Time	t <sub>f</sub>	-	20.7	-	ns	710200IIIA

Notes:

- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.



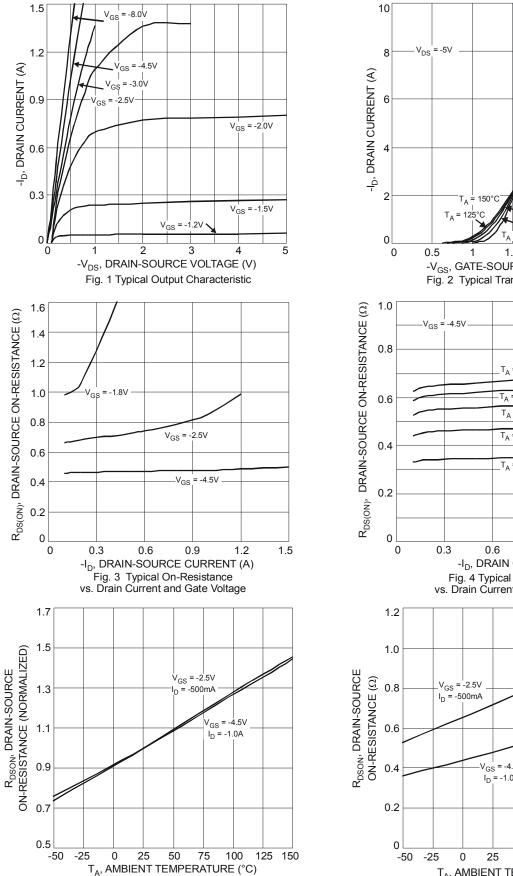


Fig. 5 On-Resistance Variation with Temperature



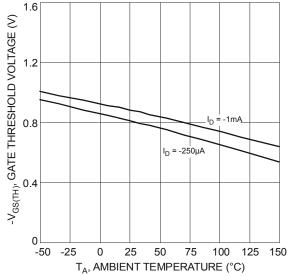
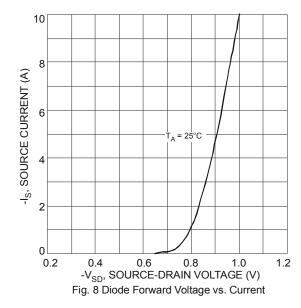
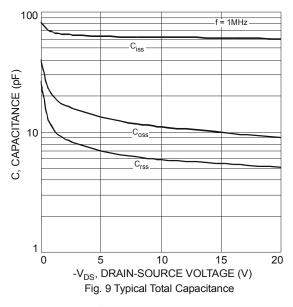


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





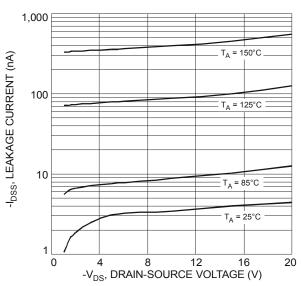


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

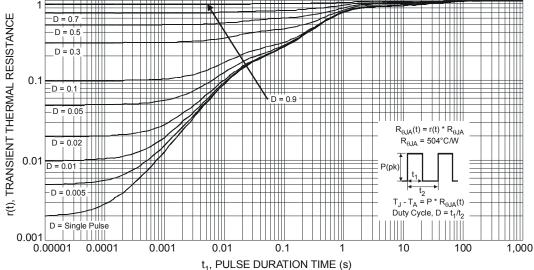
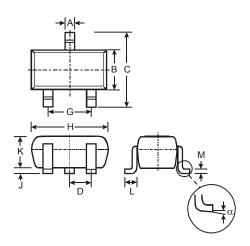


Fig. 11 Transient Thermal Response



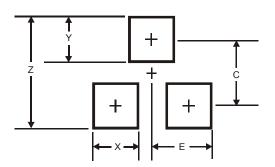
## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
Е	1.0

SOT-323

Max

0.40

1.35

1.40

2.20

0.10

1.00

0.40

0.18

Тур

0.30

1.30

2.10 0.65

1.30

2.15

0.05

0.95

0.30

0.11

Min

0.25

1.15

2.00

1.20

1.80

0.0

0.90

0.25

0.10

All Dimensions in mm

Dim

Α

В

С

D

G

K

М

α



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DMG1013UW
Document number: DS31861 Rev. 3 - 2

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